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Assistant Commissioner for Patents  
Washington, D.C. 20231

Attorney Docket No.: AM1126D1/T08910

On September 16, 1999  
TOWNSEND and TOWNSEND and CREW LLP

By: [Signature]



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

KRAMADHATI V. RAVI et al.

Application No.: 09/362,504

Filed: July 27, 1999

For: METHOD FOR REDUCING THE  
INTRINSIC STRESS OF HIGH  
DENSITY PLASMA FILMS

Examiner: Unassigned

Art Unit: 2812 1700

PRELIMINARY AMENDMENT

RECEIVED

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TECHNOLOGY CENTER 2800

Assistant Commissioner for Patents  
Washington, D.C. 20231

Sir:

Prior to examination of the above-referenced application, please enter the following amendments and remarks.

IN THE SPECIFICATION:

Please amend the specification as follows:

At page 7 lines 14, after "described in", insert --commonly assigned--;

at page 7, line 15, delete "Application 08/234,746" and insert --5,865,896--;

at page 7, line 16, delete. "filed, April 26, 1994" and insert issued February 2,

1999--.

IN THE CLAIMS:

Please amend claims 16-18; and add claims 25-35 as follows. Note that claims 19-24 remain unchanged but are reproduced here for the Examiner's convenience.

16. (AMENDED) An integrated circuit formed on a semiconductor substrate  
by the method of [claims 1, 14, or 15.];

a) flowing a process gas into a substrate processing chamber;

b) forming a plasma from said process gas;

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